



2N5551RLRPG Information



For Reference Only

Part Number 2N5551RLRPG
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - Bipolar (BJT) - Single

Description TRANS NPN 160V 0.6A TO-92

Package TO-226-3, TO-92-3 (TO-226AA) (Formed Leads)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









2N5551RLRPG Specifications

Manufacturer Part Number2N5551RLRPGManufacturerON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - Bipolar (BJT) - SinglePackageTO-226-3, TO-92-3 (TO-226AA) (Formed Leads)Series-Transistor TypeNPNCurrent - Collector (Ic) (Max)600mAVoltage - Collector Emitter Breakdown (Max)160VVce Saturation (Max) @ Ib, Ic200mV @ 5mA, 50mACurrent - Collector Cutoff (Max)50nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 10mA, 5VPower - Max625mWFrequency - Transition300MHz	•		
Category Discrete Semiconductor Products Transistors - Bipolar (BJT) - Single Package TO-226-3, TO-92-3 (TO-226AA) (Formed Leads) Series - Transistor Type NPN Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) DC Current Gain (hFE) (Min) @ Ic, Vce Power - Max Discrete Semiconductor Products Transistors - Bipolar (BJT) - Single TO-226-3, TO-92-3 (TO-226AA) (Formed Leads) - Universe Semiconductor Products Transistors - Bipolar (BJT) - Single TO-226-3, TO-92-3 (TO-226AA) (Formed Leads) - Universe Semiconductor Products To-226-3, TO-92-3 (TO-226AA) (Formed Leads) - To-226-3, TO-92-3 (TO-226AA) (Formed Leads) - Transistor Type Supplies Semiconductor Products To-226-3, TO-92-3 (TO-226AA) (Formed Leads) - Transistor Type Supplies Semiconductor Products To-226-3, TO-92-3 (TO-226AA) (Formed Leads) - Transistor Type Supplies Supplie	Manufacturer Part Number	2N5551RLRPG	
Transistors - Bipolar (BJT) - Single TO-226-3, TO-92-3 (TO-226AA) (Formed Leads) Series - Transistor Type NPN Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Vce Saturation (Max) @ Ib, Ic 200mV @ 5mA, 50mA Current - Collector Cutoff (Max) DC Current Gain (hFE) (Min) @ Ic, Vce Power - Max Transistors - Bipolar (BJT) - Single TO-226-3, TO-92-3 (TO-226AA) (Formed Leads) - Universe Suppose	Manufacturer	ON Semiconductor	
Package TO-226-3, TO-92-3 (TO-226AA) (Formed Leads) Series - Transistor Type NPN Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Vce Saturation (Max) @ Ib, Ic 200mV @ 5mA, 50mA Current - Collector Cutoff (Max) DC Current Gain (hFE) (Min) @ Ic, Vce 80 @ 10mA, 5V Power - Max 625mW	Category	Discrete Semiconductor Products	
Series - Transistor Type NPN Current - Collector (Ic) (Max) 600mA Voltage - Collector Emitter Breakdown (Max) 160V Vce Saturation (Max) @ Ib, Ic 200mV @ 5mA, 50mA Current - Collector Cutoff (Max) 50nA (ICBO) DC Current Gain (hFE) (Min) @ Ic, Vce 80 @ 10mA, 5V Power - Max 625mW		Transistors - Bipolar (BJT) - Single	
Transistor Type Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Vce Saturation (Max) @ Ib, Ic Current - Collector Cutoff (Max) DC Current Gain (hFE) (Min) @ Ic, Vce Power - Max NPN 600mA 160V 200mV @ 5mA, 50mA 50nA (ICBO) 80 @ 10mA, 5V 625mW	Package	TO-226-3, TO-92-3 (TO-226AA) (Formed Leads)	
Current - Collector (Ic) (Max) Voltage - Collector Emitter Breakdown (Max) Vce Saturation (Max) @ Ib, Ic 200mV @ 5mA, 50mA Current - Collector Cutoff (Max) 50nA (ICBO) DC Current Gain (hFE) (Min) @ Ic, Vce 80 @ 10mA, 5V Power - Max 625mW	Series	-	
Voltage - Collector Emitter Breakdown (Max) Vce Saturation (Max) @ Ib, Ic 200mV @ 5mA, 50mA Current - Collector Cutoff (Max) 50nA (ICBO) DC Current Gain (hFE) (Min) @ Ic, Vce 80 @ 10mA, 5V Power - Max 625mW	Transistor Type	NPN	
Vce Saturation (Max) @ Ib, Ic200mV @ 5mA, 50mACurrent - Collector Cutoff (Max)50nA (ICBO)DC Current Gain (hFE) (Min) @ Ic, Vce80 @ 10mA, 5VPower - Max625mW	Current - Collector (Ic) (Max)	600mA	
Current - Collector Cutoff (Max) DC Current Gain (hFE) (Min) @ Ic, Vce 80 @ 10mA, 5V Power - Max 625mW	Voltage - Collector Emitter Breakdown (Max)	160V	
DC Current Gain (hFE) (Min) @ Ic, Vce 80 @ 10mA, 5V Power - Max 625mW	Vce Saturation (Max) @ Ib, Ic	200mV @ 5mA, 50mA	
Power - Max 625mW	Current - Collector Cutoff (Max)	50nA (ICBO)	
	DC Current Gain (hFE) (Min) @ Ic, Vce	80 @ 10mA, 5V	
Frequency - Transition 300MHz	Power - Max	625mW	
	Frequency - Transition	300MHz	
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Operating Temperature	-55°C ~ 150°C (TJ)	
Mounting Type Through Hole	Mounting Type	Through Hole	
Package / Case TO-226-3, TO-92-3 (TO-226AA) (Formed Leads)	Package / Case	TO-226-3, TO-92-3 (TO-226AA) (Formed Leads)	
Supplier Device Package TO-92-3	Supplier Device Package	TO-92-3	
Report errors?			Report errors?

2N5551RLRPG Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

2N5551RLRPG Payment Methods



















2N5551RLRPG Shipping Methods













If you have any question about 2N5551RLRPG, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com